10-bit D-type flip-flop; positive-edge trigger (3-State)

74ABT821

FEATURES

- High speed parallel registers with positive edge-triggered D-type flip-flops
- Ideal where high speed, light loading, or increased fan-in are required with MOS microprocessors
- Output capability: +64mA/–32mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000 V per MIL STD 883 Method 3015 and 200 V per Machine Model
- Power-up 3-State
- Power-up Reset

DESCRIPTION

The 74ABT821 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT821 Bus interface Register is designed to eliminate the extra packages required to buffer existing registers and provide extra data width for wider data/address paths of buses carrying parity.

The 74ABT821 is a buffered 10-bit wide version of the 74ABT374/74ABT534 functions.

The 74ABT821 is a 10-bit, edge triggered register coupled to ten 3-State output buffers. The two sections of the device are controlled independently by the clock (CP) and Output Enable ($\overline{OE}$) control gates.

The register is fully edge triggered. The state of each D input, one set-up time before the Low-to-High clock transition is transferred to the corresponding flip-flop's Q output.

The 3-State output buffers are designed to drive heavily loaded 3-State buses, MOS memories, or MOS microprocessors.

The active Low Output Enable ($\overline{OE}$) controls all ten 3-State buffers independent of the register operation. When $\overline{OE}$ is Low, the data in the register appears at the outputs. When $\overline{OE}$ is High, the outputs are in high impedance "off" state, which means they will neither drive nor load the bus.

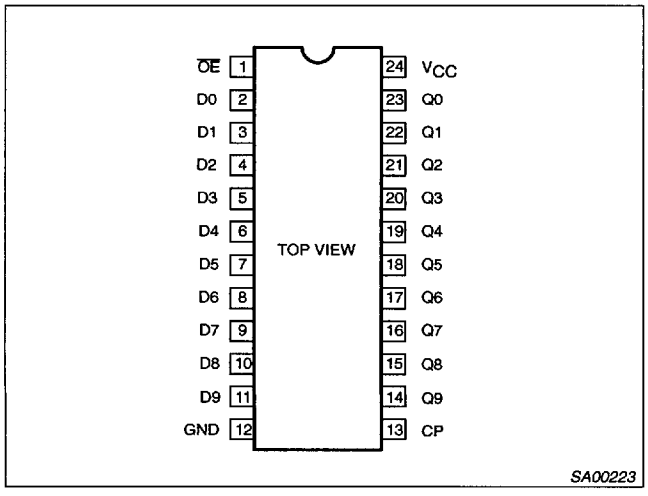
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T_{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay CP to Qn	C_L = 50pF; V_{CC} = 5V	4.6	ns
C_{IN}	Input capacitance	V_I = 0V or V_{CC}	4	pF
C_{OUT}	Output capacitance	Outputs disabled; V_O = 0V or V_{CC}	7	pF
I_{CCZ}	Total supply current	Outputs disabled; V_{CC} =5.5V	500	nA

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
24-Pin Plastic DIP	–40°C to +85°C	74ABT821 N	74ABT821 N	SOT222-1
24-Pin plastic SO	–40°C to +85°C	74ABT821 D	74ABT821 D	SOT137-1
24-Pin Plastic SSOP Type II	–40°C to +85°C	74ABT821 DB	74ABT821 DB	SOT340-1
24-Pin Plastic TSSOP Type I	–40°C to +85°C	74ABT821 PW	74ABT821PW DH	SOT355-1

PIN CONFIGURATION



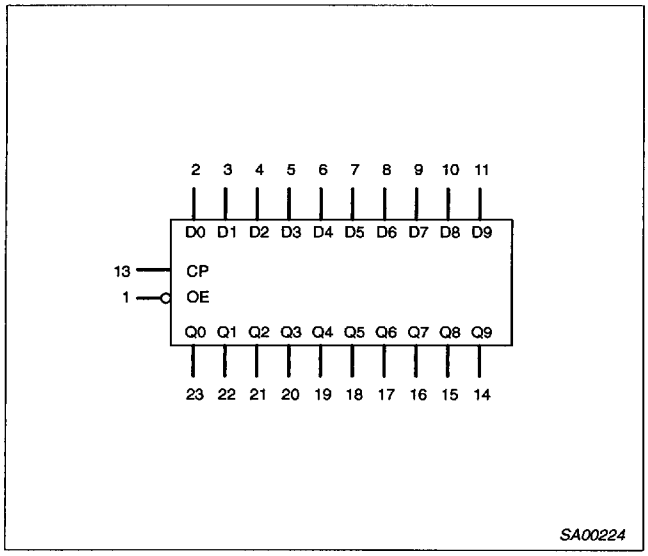
PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1	$\overline{OE}$	Output enable input (active-Low)
2, 3, 4, 5, 6, 7, 8, 9, 10, 11	D0-D9	Data inputs
23, 22, 21, 20, 19, 18, 17, 16, 15, 14	Q0-Q9	Data outputs
13	CP	Clock pulse input (active rising edge)
10	GND	Ground (0V)
20	V_{CC}	Positive supply voltage

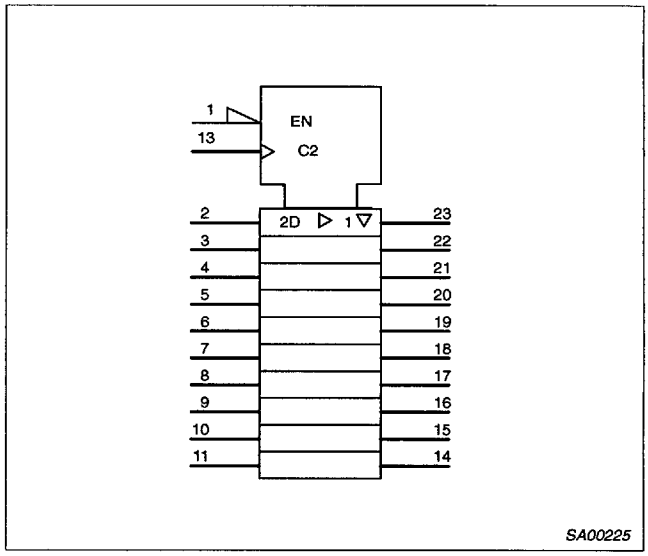
10-bit D-type flip-flop; positive-edge trigger (3-State)

74ABT821

LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)

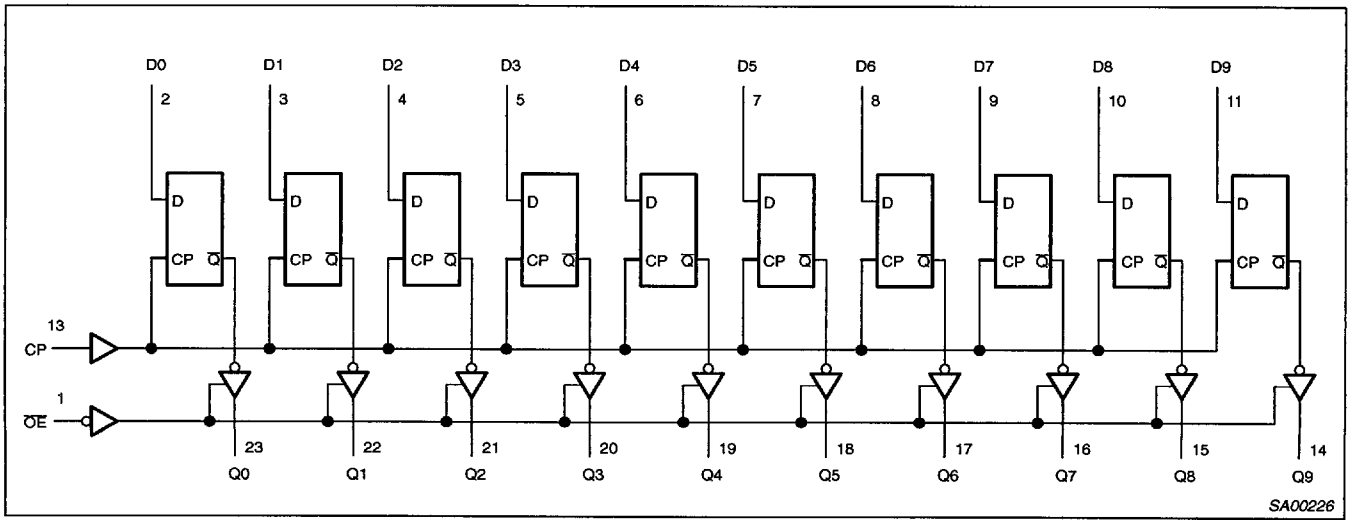


FUNCTION TABLE

INPUTS			INTERNAL	OUTPUTS	OPERATING MODE
$\overline{OE}$	CP	Dn	REGISTER	Q0 – Q9	
L L	↑ ↑	l h	L H	L H	Load and read register
L	↕	X	NC	NC	Hold
H H	↕ ↑	X Dn	NC Dn	Z Z	Disable outputs

H = High voltage level
h = High voltage level one set-up time prior to the Low-to-High clock transition
L = Low voltage level
l = Low voltage level one set-up time prior to the Low-to-High clock transition
NC = No change
X = Don't care
Z = High impedance "off" state
↑ = Low to High clock transition
↕ = Not a Low-to-High clock transition

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS[1, 2]

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		−0.5 to +7.0	V
I_{IK}	DC input diode current	$V_I < 0$	−18	mA
V_I	DC input voltage[3]		−1.2 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	−50	mA
V_{OUT}	DC output voltage[3]	output in Off or High state	−0.5 to +5.5	V
I_{OUT}	DC output current	output in Low state	128	mA
T_{stg}	Storage temperature range		−65 to 150	°C

NOTES:
1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		Min	Max	
V_{CC}	DC supply voltage	4.5	5.5	V
V_I	Input voltage	0	V_{CC}	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Low-level input voltage		0.8	V
I_{OH}	High-level output current		−32	mA
I_{OL}	Low-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_{amb}	Operating free-air temperature range	−40	+85	°C

DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			T_{amb} = +25°C			T_{amb} = –40°C to +85°C		
			Min	Typ	Max	Min	Max	
V_{IK}	Input clamp voltage	V_{CC} = 4.5V; I_{IK} = –18mA		–0.9	–1.2		–1.2	V
V_{OH}	High-level output voltage	V_{CC} = 4.5V; I_{OH} = –3mA; V_I = V_{IL} or V_{IH}	2.5	2.9		2.5		V
		V_{CC} = 5.0V; I_{OH} = –3mA; V_I = V_{IL} or V_{IH}	3.0	3.4		3.0		V
		V_{CC} = 4.5V; I_{OH} = –32mA; V_I = V_{IL} or V_{IH}	2.0	2.4		2.0		V
V_{OL}	Low-level output voltage	V_{CC} = 4.5V; I_{OL} = 64mA; V_I = V_{IL} or V_{IH}		0.42	0.55		0.55	V
V_{RST}	Power-up output low voltage[3]	V_{CC} = 5.5V; I_O = 1mA; V_I = GND or V_{CC}		0.13	0.55		0.55	V
I_I	Input leakage current	V_{CC} = 5.5V; V_I = GND or 5.5V		±0.01	±1.0		±1.0	µA
I_{OFF}	Power-off leakage current	V_{CC} = 0.0V; V_O or $V_I \leq$ 4.5V		±5.0	±100		±100	µA
I_{PU}/I_{PD}	Power-up/down 3-State output current[4]	V_{CC} = 2.0V; V_O = 0.5V; V_I = GND or V_{CC}; V_{OE} = V_{CC}		±5.0	±50		±50	µA
I_{OZH}	3-State output High current	V_{CC} = 5.5V; V_O = 2.7V; V_I = V_{IL} or V_{IH}		5.0	50		50	µA
I_{OZL}	3-State output Low current	V_{CC} = 5.5V; V_O = 0.5V; V_I = V_{IL} or V_{IH}		–5.0	–50		–50	µA
I_{CEX}	Output High leakage current	V_{CC} = 5.5V; V_O = 5.5V; V_I = GND or V_{CC}		5.0	50		50	µA
I_O	Output current[1]	V_{CC} = 5.5V; V_O = 2.5V	–50	–100	–180	–50	–180	mA
I_{CCH}	Quiescent supply current	V_{CC} = 5.5V; Outputs High, V_I = GND or V_{CC}		0.5	250		250	µA
I_{CCL}		V_{CC} = 5.5V; Outputs Low, V_I = GND or V_{CC}		25	38		38	mA
I_{CCZ}		V_{CC} = 5.5V; Outputs 3-State; V_I = GND or V_{CC}		0.5	250		250	µA
ΔI_{CC}	Additional supply current per input pin[2]	V_{CC} = 5.5V; one input at 3.4V, other inputs at V_{CC} or GND		0.5	1.5		1.5	mA

NOTES:
1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
2. This is the increase in supply current for each input at 3.4V.
3. For valid test results, data must not be loaded into the flip-flops (or latches) after applying the power.
4. This parameter is valid for any V_{CC} between 0V and 2.1V with a transition time of up to 10msec. For V_{CC} = 2.1V to V_{CC} = 5V ± 10%, a transition time of up to 100µsec is permitted.

AC CHARACTERISTICS

GND = 0V, t_R = t_F = 2.5ns, C_L = 50pF, R_L = 500Ω

SYMBOL	PARAMETER	WAVEFORM	LIMITS					UNIT
			T_{amb} = +25°C V_{CC} = +5.0V			T_{amb} = -40 to +85°C V_{CC} = +5.0V ±0.5V		
			Min	Typ	Max	Typ	Max	
f_{MAX}	Maximum clock frequency	1	125	185		125		ns
t_{PLH} t_{PHL}	Propagation delay CP to Qn	1	2.1 2.8	4.1 4.6	5.6 6.2	2.1 2.8	6.2 6.7	ns
t_{PZH} t_{PZL}	Output enable time to High and Low level	3 4	1.0 2.2	3.0 4.1	4.5 5.6	1.0 2.2	5.3 6.3	ns
t_{PHZ} t_{PLZ}	Output disable time from High and Low level	3 4	2.7 2.8	4.7 4.6	6.2 6.1	2.7 2.8	6.7 6.5	ns

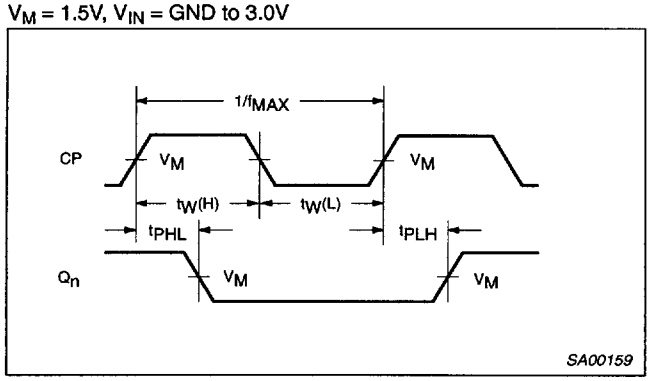
AC SETUP REQUIREMENTS

GND = 0V, $t_R = t_F$ = 2.5ns, C_L = 50pF, R_L = 500Ω

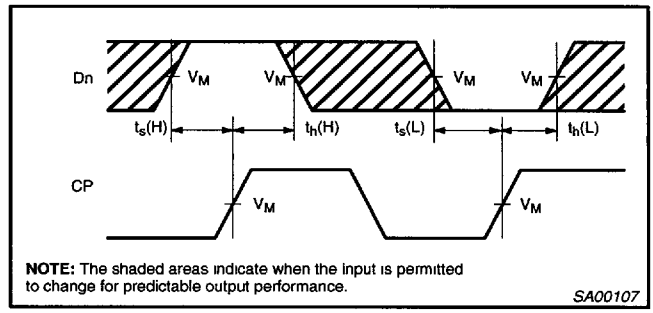
SYMBOL	PARAMETER	WAVEFORM	LIMITS			UNIT
			T_{amb} = +25°C, V_{CC} = +5.0V		T_{amb} = -40 to +85°C, V_{CC} = +5.0V ±0.5V	
			Min	Typ	Min	
$t_s(H)$ $t_s(L)$	Setup time, High or Low Dn to CP	2	2.1 2.1	0.5 0.3	2.1 2.1	ns
$t_h(H)$ $t_h(L)$	Hold time, High or Low Dn to CP	2	1.3 1.3	0.0 –0.3	1.3 1.3	ns
$t_w(H)$ $t_w(L)$	CP pulse width High or Low	1	2.9 3.8	1.8 2.8	2.9 3.8	ns

AC WAVEFORMS

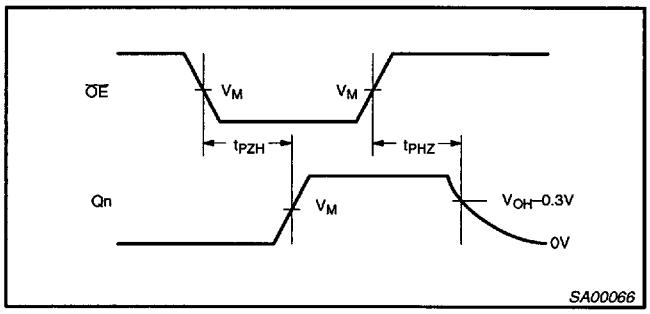
V_M = 1.5V, V_{IN} = GND to 3.0V



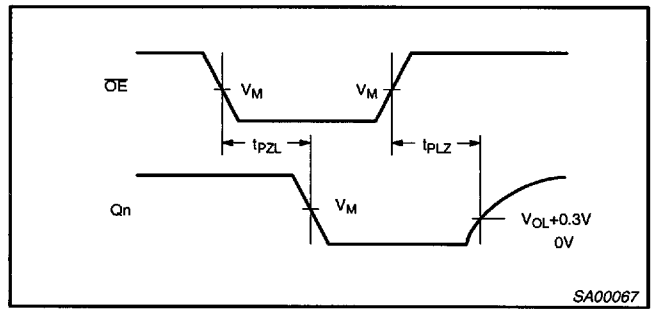
Waveform 1. Propagation Delay, Clock Input to Output, Clock Pulse Width, and Maximum Clock Frequency



Waveform 2. Data Setup and Hold Times

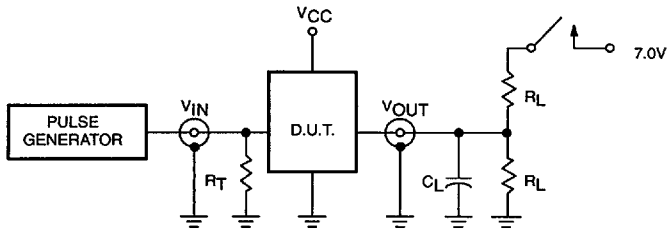


Waveform 3. 3–State Output Enable Time to High Level and Output Disable Time from High Level

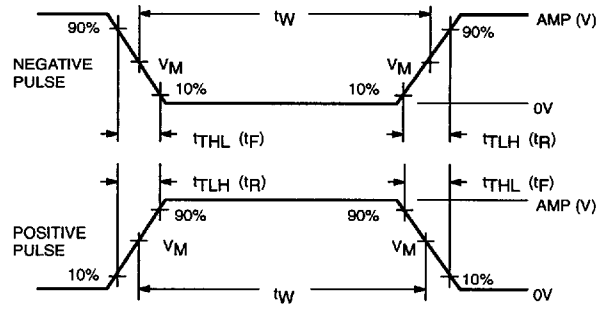


Waveform 4. 3–State Output Enable Time to Low Level and Output Disable Time from Low Level

TEST CIRCUIT AND WAVEFORM



Test Circuit for 3-State Outputs



V_M = 1.5V

Input Pulse Definition

SWITCH POSITION

TEST	SWITCH
t_{PLZ}	closed
t_{PZL}	closed
All other	open

DEFINITIONS

R_L = Load resistor; see AC CHARACTERISTICS for value.

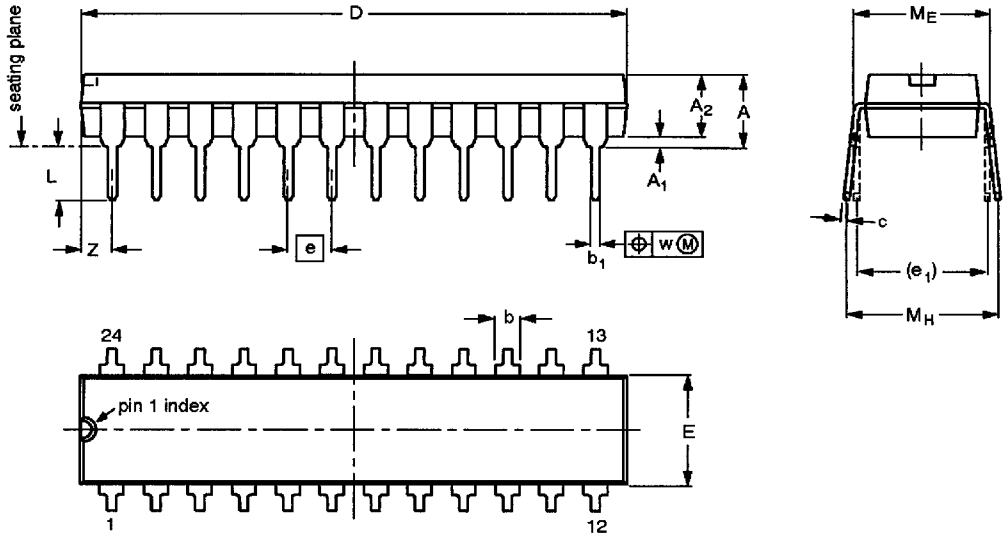
C_L = Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

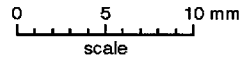
R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

FAMILY	INPUT PULSE REQUIREMENTS				
	Amplitude	Rep. Rate	t_W	t_R	t_F
74ABT	3.0V	1MHz	500ns	2.5ns	2.5ns

SA00012

DIP24: plastic dual in-line package; 24 leads (300 mil) **SOT222-1**





DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

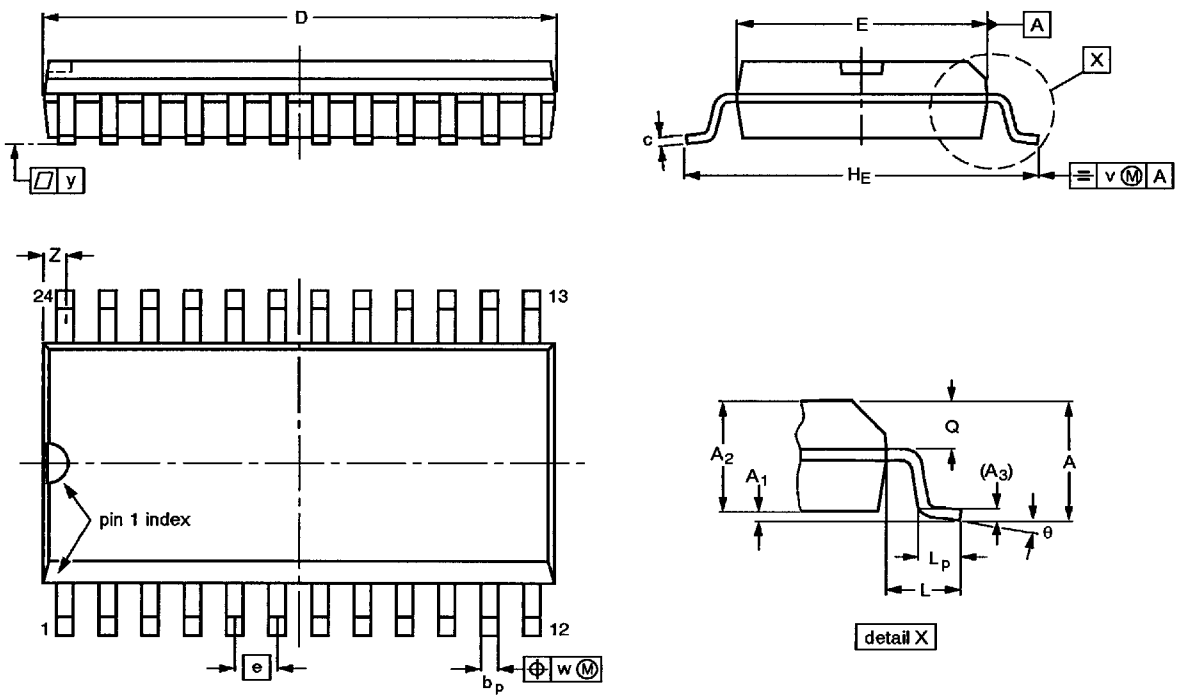
UNIT	A max.	A_1 min.	A_2 max.	b	b_1	c	$D^{(1)}$	$E^{(1)}$	e	e_1	L	M_E	M_H	w	$Z^{(1)}$ max.
mm	4.70	0.38	3.94	1.63 1.14	0.56 0.43	0.36 0.25	31.9 31.5	6.73 6.48	2.54	7.62	3.51 3.05	8.13 7.62	10.03 7.62	0.25	2.05
inches	0.185	0.015	0.155	0.064 0.045	0.022 0.017	0.014 0.010	1.256 1.240	0.265 0.255	0.100	0.300	0.138 0.120	0.32 0.30	0.395 0.300	0.01	0.081

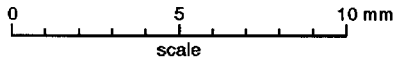
Note

1. Plastic or metal protrusions of 0.01 inches maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT222-1		MS-001AF				95-03-11

SO24: plastic small outline package; 24 leads; body width 7.5 mm — SOT137-1





DIMENSIONS (inch dimensions are derived from the original mm dimensions)

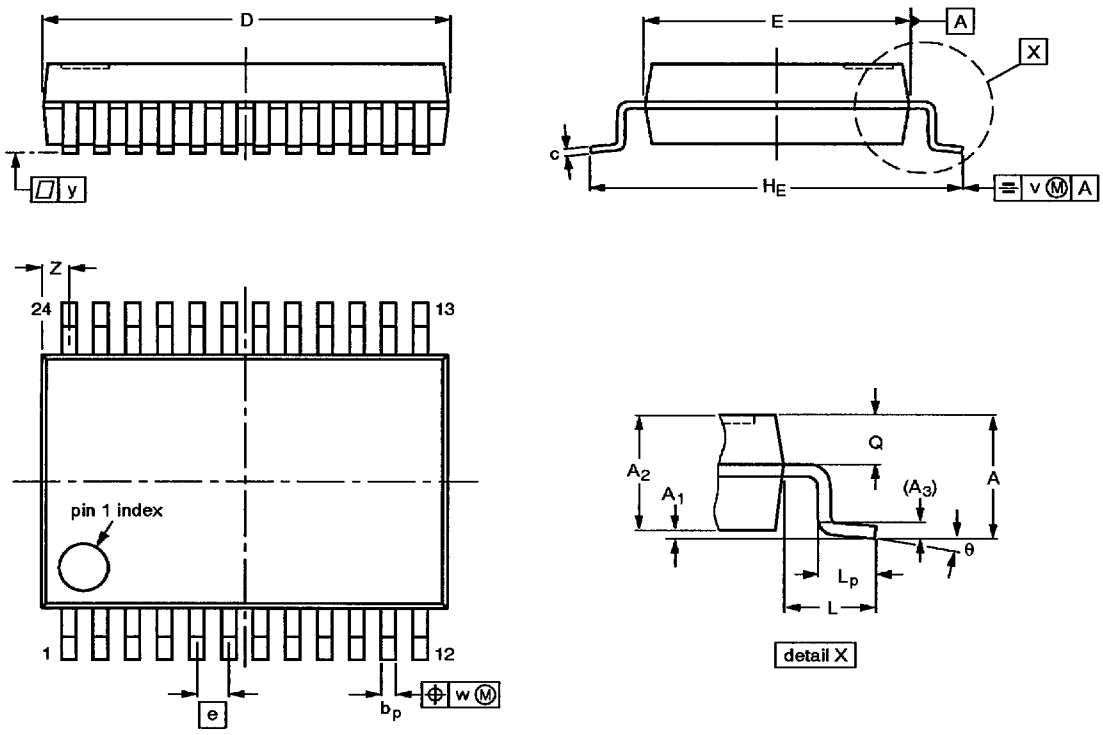
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	15.6 15.2	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8° 0°
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.61 0.60	0.30 0.29	0.050	0.42 0.39	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

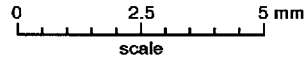
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT137-1	075E05	MS-013AD				~~92-11-17~~ 95-01-24

SSOP24: plastic shrink small outline package; 24 leads; body width 5.3 mm **SOT340-1**





DIMENSIONS (mm are the original dimensions)

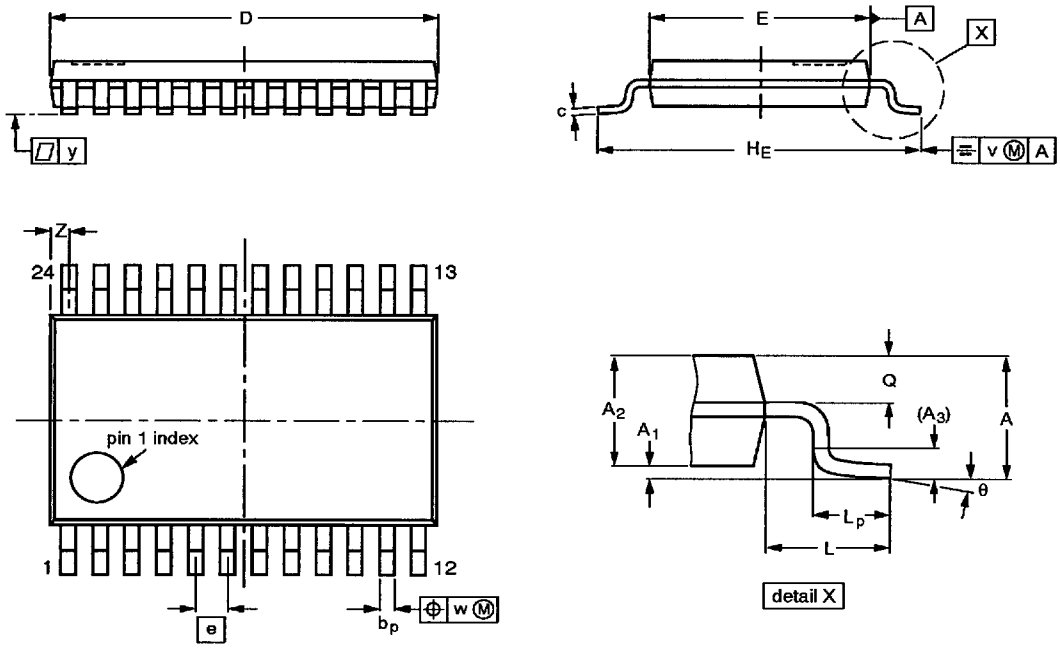
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	8.4 8.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.8 0.4	8° 0°

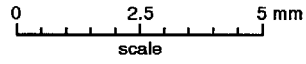
Note

1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT340-1		MO-150AG				~~93-09-08~~ 95-02-04

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm **SOT355-1**





DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	7.9 7.7	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT355-1		MO-153AD				~~93-06-16~~ 95-02-04